

PNP switching transistor

PMSS3906

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching in e.g. telephony and professional communication equipment.

DESCRIPTION

PNP switching transistor in an SC-70; SOT323 plastic package. NPN complement: PMSS3904.

MARKING

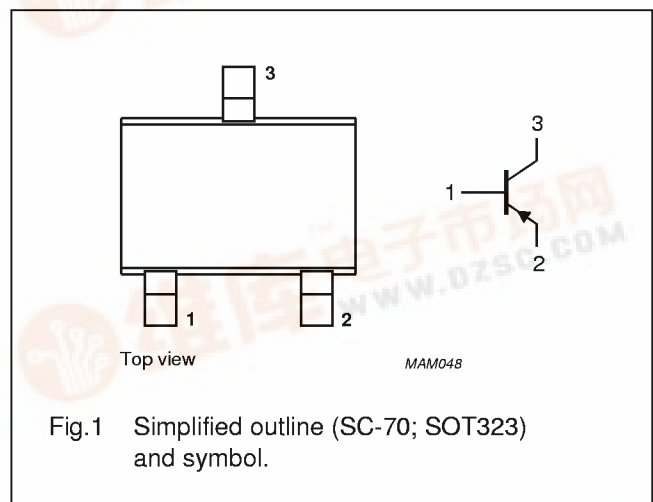
TYPE NUMBER	MARKING CODE ⁽¹⁾
PMSS3906	*06

Note

- * = - : Made in Hong Kong.
* = t : Made in Malaysia.

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	−40	V
V_{CEO}	collector-emitter voltage	open base	—	−40	V
V_{EBO}	emitter-base voltage	open collector	—	−5	V
I_C	collector current (DC)		—	−100	mA
I_{CM}	peak collector current		—	−200	mA
I_{BM}	peak base current		—	−100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	—	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		—	150	°C
T_{amb}	operating ambient temperature		−65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

PNP switching transistor

PMSS3906

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	625	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = -30\text{ V}$	–	–50	nA
		$I_E = 0; V_{CB} = -30\text{ V}; T_j = 150\text{ °C}$	–	–10	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = -5\text{ V}$	–	–50	nA
h_{FE}	DC current gain	$V_{CE} = -1\text{ V}$ $I_C = -0.1\text{ mA}$	60	–	
		$I_C = -1\text{ mA}$	80	–	
		$I_C = -10\text{ mA}$	100	300	
		$I_C = -50\text{ mA}; \text{note 1}$	60	–	
		$I_C = -100\text{ mA}; \text{note 1}$	30	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–250	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}; \text{note 1}$	–	–400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10\text{ mA}; I_B = -1\text{ mA}$	–	–850	mV
		$I_C = -50\text{ mA}; I_B = -5\text{ mA}; \text{note 1}$	–	–950	mV
C_c	collector capacitance	$I_E = I_C = 0; V_{CB} = -5\text{ V}; f = 1\text{ MHz}$	–	4.5	pF
C_e	emitter capacitance	$I_C = I_E = 0; V_{EB} = -0.5\text{ V}; f = 1\text{ MHz}$	–	14	pF
f_T	transition frequency	$I_E = -10\text{ mA}; V_{CB} = -20\text{ V}; f = 100\text{ MHz}$	150	–	MHz
F	noise figure	$I_C = -100\text{ }\mu\text{A}; V_{CE} = -5\text{ V}; R_S = 1\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}$	–	4	dB

Switching times (between 10% and 90% levels); see Fig.2

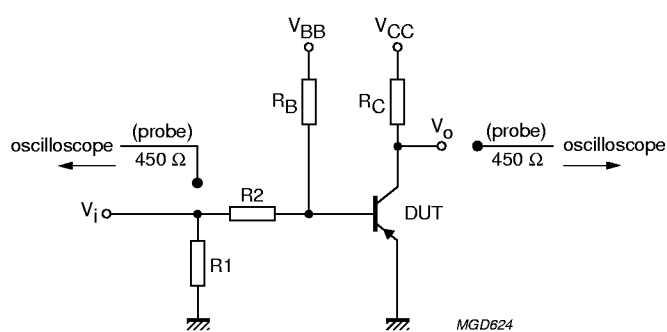
t_{on}	turn-on time	$I_{Con} = -10\text{ mA}; I_{Bon} = -1\text{ mA}; I_{Boff} = 1\text{ mA}$	–	100	ns
t_d	delay time		–	50	ns
t_r	rise time		–	50	ns
t_{off}	turn-off time		–	700	ns
t_s	storage time		–	600	ns
t_f	fall time		–	100	ns

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

PNP switching transistor

PMSS3906



$V_i = -5 \text{ V}$; $T = 500 \text{ } \mu\text{s}$; $t_p = 10 \text{ } \mu\text{s}$; $t_r = t_f \leq 3 \text{ ns}$.
 $R_1 = 56 \text{ } \Omega$; $R_2 = 2.5 \text{ k}\Omega$; $R_B = 3.9 \text{ k}\Omega$; $R_C = 270 \text{ } \Omega$.
 $V_{BB} = 1.9 \text{ V}$; $V_{CC} = 3 \text{ V}$.
 Oscilloscope input impedance $Z_i = 50 \text{ } \Omega$.

Fig.2 Test circuit for switching times.

PNP switching transistor

PMSS3906

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323

